AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on line 7 of page 16 as follows:

Although the present invention ~~specifiely~~ specifically demonstrates nanostructured void/column Si films being capable of synthesizing, immobilizing and dispersing metal nanoparticles when they are simply in contact with a pure metal salt solution further generalizations are possible. For instance, the nanostructured film/surface material is not restricted to be Si. It can be, but not limited to, an element in the same group as Si such as C, Ge, Sn, Pb. Or it can be, but not limited to, a III-V compound such as boron nitride, gallium arsenide, indium arsenide, indium phosphide, aluminum arsenide, gallium phosphide, gallium nitride, or II-VI compound, such as zinc oxide, zinc sulfide, zinc selenide, cadmium sulfide, cadmium selenide, cadmium telluride, or various other compounds such as titanium, titanium oxide, aluminum, aluminum oxide, ~~nickle~~ nickel, ~~nickle~~ nickel oxide, chrome, chrome oxide, or elements. The nanostructured film or surface material can be comprised of nano-elements such as nanowires, nanorods, nanocolumns, nanotubes, or nanoparticles or various shapes. Or, the nanostructured surface or film can be a nanotextured surface with roughness, features or patterns at the nanometer scale (1 nm to 500 nm). The nanostructured and/or nanotextured surface may be porous, with a typical pore size of 1 to 500 nm.